# **CPH3459**

# Power MOSFET 200V, 3.7Ω, 0.5A, Single N-Channel



http://onsemi.com

#### **Features**

- On-resistance RDS(on)1= $2.8\Omega$  (typ)
- 4V drive
- Halogen free compliance

- Input Capacitance Ciss=90pF (typ)
- Protection Diode in

## **Specifications**

**Absolute Maximum Ratings** at Ta = 25°C

Parameter	Symbol	Conditions	Value	Unit
Drain to Source Voltage	VDSS		200	V
Gate to Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		0.5	Α
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	2	Α
Power Dissipation	PD	When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm)	1.0	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## **Thermal Resistance Ratings**

Parameter	Symbol	Value	Unit
Junction to Ambient	$R_{\theta JA}$	125	°C/W
When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm)			

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### **Electrical Characteristics** at Ta = 25°C

Parameter	Symbol	Conditions	Value			
			min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	200			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =200V, V <sub>GS</sub> =0V			1	μΑ
Gate to Source Leakage Current	IGSS	$V_{GS}=\pm 16V, V_{DS}=0V$			±10	μА
Gate Threshold Voltage	VGS(th)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.2		2.6	V
Forward Transconductance	9FS	V <sub>DS</sub> =10V, I <sub>D</sub> =0.25A		0.8		S
Static Drain to Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> =0.25A, V <sub>GS</sub> =10V		2.8	3.7	Ω
	R <sub>DS</sub> (on)2	I <sub>D</sub> =0.25A, V <sub>GS</sub> =4V		2.9	4.1	Ω

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#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet.

# **CPH3459**

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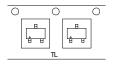
Parameter Symbol Conditions		0 101	Value			Unit
	min	Тур	max			
Input Capacitance	Ciss	V <sub>DS</sub> =20V, f=1MHz		90		pF
Output Capacitance	Coss			10		pF
Reverse Transfer Capacitance	Crss			6		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit		4		ns
Rise Time	t <sub>r</sub>			3.5		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)			14		ns
Fall Time	t <sub>f</sub>			45		ns
Total Gate Charge	Qg	V <sub>DS</sub> =100V, V <sub>GS</sub> =10V, I <sub>D</sub> =0.5A		2.4		nC
Gate to Source Charge	Qgs			0.3		nC
Gate to Drain "Miller" Charge	Qgd	]		0.8		nC
Forward Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> =0.5A, V <sub>GS</sub> =0V		0.82	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# **Ordering & Package Information**

Device	Package	Shipping	note
CPH3459-TL-W	CPH3, SC-59 SOT-23, TO-236	3,000 pcs. / reel	Pb-Free and Halogen Free

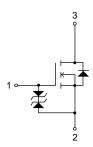
# Packing Type:TL



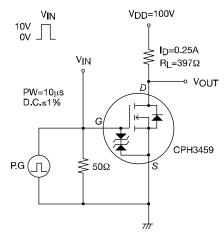
# Marking

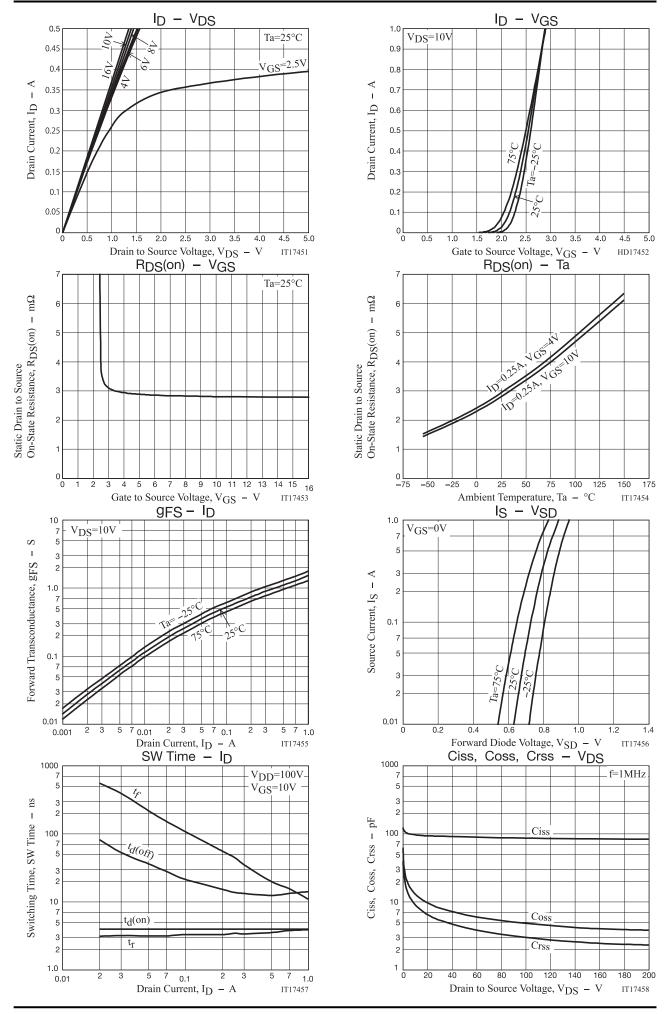


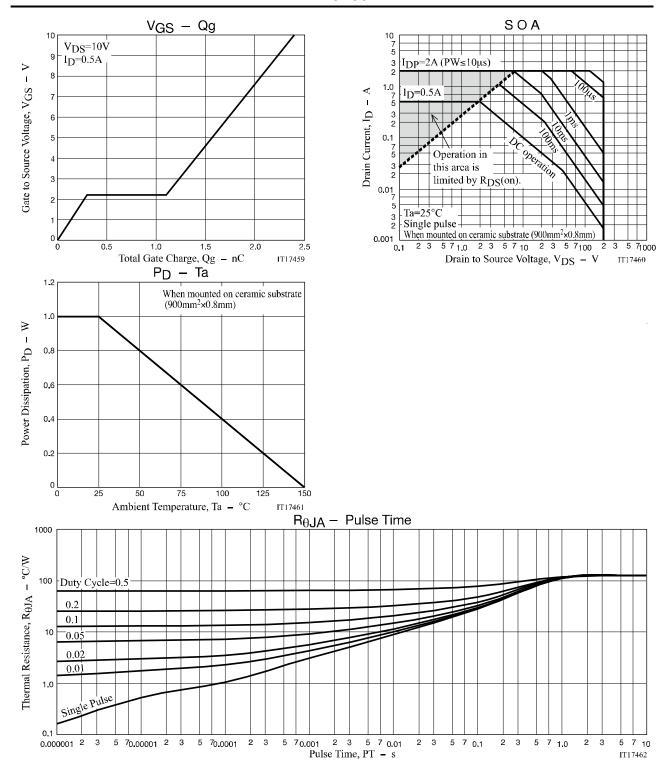
# **Electrical Connection**



# **Switching Time Test Circuit**







# **Package Dimensions**

CPH3459-TL-W

#### CPH3

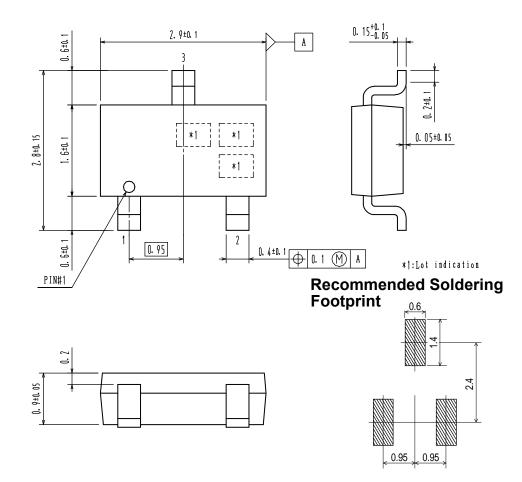
CASE 318BA ISSUE O

unit: mm

1: Gate

2: Source

3: Drain



Note on usage: Since the CPH3459 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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